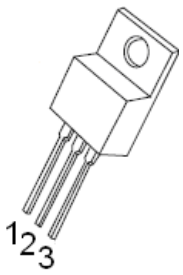
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220-3L Plastic-Encapsulate Transistors

KTB1366 TRANSISTOR (PNP)

TO-220-3L

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

- Low Collector Saturation Voltage
- Complementary to KTD2058

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current	-3	A
P_C	Collector Power Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	63	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-50mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA,I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V,I_E=0			-100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-7V,I_C=0			-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-0.5A	60		200	
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-3A	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A,I_B=-0.2A			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-0.5A			-1	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz		150		pF
Transition frequency	f_T	V_{CE}=-5V,I_C=-0.5A		9		MHz

CLASSIFICATION OF $h_{FE\ (1)}$

RANK	O	Y
RANGE	60-120	100-200